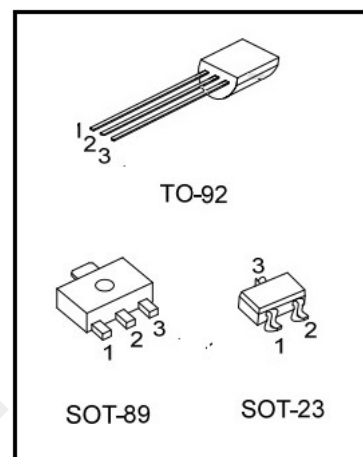


FEATURES

- Complementary to SS8050
- Package: TO-92/SOT-23/SOT-89

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector-base voltage	BV_{CBO}	-40	V
Collector-emitter voltage	BV_{CEO}	-25	V
Emitter-base voltage	BV_{EBO}	-5	V
Collector current	I_{CM}	-1.5	A
Collector Power Dissipation	P_C	TO-92	1.0
		SOT-23	0.3
		SOT-89	0.5
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~+150	°C



Package	Pin assignment		
	1	2	3
TO-92	E	B	C
SOT-89	B	C	E
SOT-23	B	E	C

Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = -100\mu A, I_E = 0$	-40			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1mA, I_B = 0$	-25			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -100\mu A, I_C = 0$	-5			V
collector-base cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-0.1	μA
collector-emitter cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$			-0.1	μA
emitter-base cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	H_{FE}	$V_{CE} = -1V, I_C = -100mA$	120		400	
		$V_{CE} = -1V, I_C = -800mA$	50			
collector-emitter saturation voltage	V_{CESAT}	$I_C = -800mA, I_B = -80mA$			-0.6	V
Base-Emitter Saturation Voltage	V_{BESAT}	$I_C = -800mA, I_B = -80mA$			-1.2	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 50mA$	100			MHz

Classification of H_{FE}

Rank	SS8550-L	SS8550-H	SS8550-J
Range	120-200	200-350	300-400